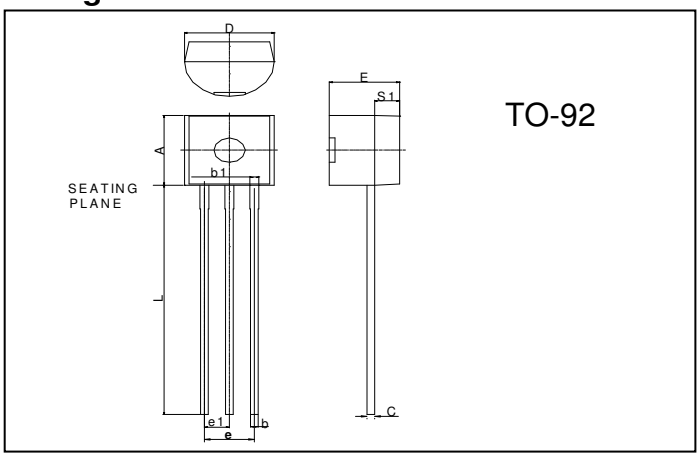
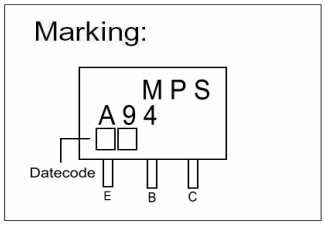
GMPSA94 PNP EPITAXIAL PLANAR TRANSISTOR

Description
The GMPSA94 is designed for application that requires high voltage.

Features
*High Breakdown Voltage:-400(Min) at IC=-1mA
*High current .Gain :IC=-300mA at 25℃
*Complementary to GMPSA44

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S_1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b_1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings (Ta = 25℃,unless otherwise specified)

Parameter		Ratings	Unit
Collector to Base Voltage	V_{CBO}	-400	V
Collector to Emitter Voltage	V_{CEO}	-400	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collect Current(DC)	I_C	-300	mA
Junction Temperature	Tj	+150	℃
Storage Temperature Range	T_{STG}	-55 ~ +150	℃
Total Power Dissipation	P_D	625	mW

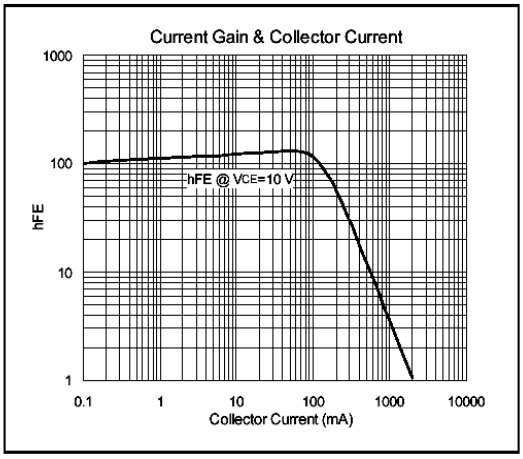
Electrical Characteristics(Ta = 25℃,unless otherwise specified)

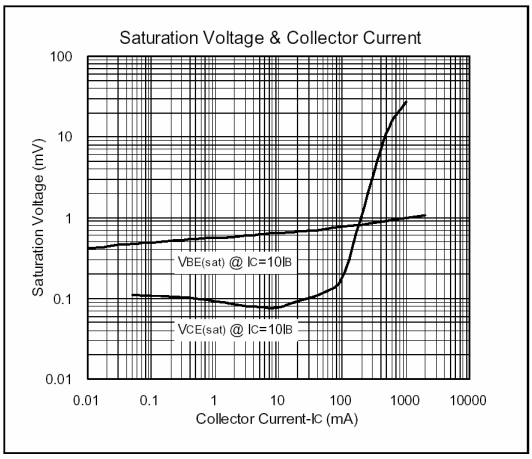
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-400	-	-	V	IC=-100uA,IE=0
BVCEO	-400	-	-	V	IC=-1mA ,IB=0
BVEBO	-6	-	-	V	IE=-10uA ,IC=0
ICBO	-	-	-100	nA	VCB=-400V,IE=0
IEBO	-	-	-100	nA	VEB=-4V,IC=0
ICES	-	-	-500	nA	VCE=-400V,VBE=0
VCE(sat)1	-	-	-350	mV	IC=-1.0mA, IB= -0.1mA
VCE(sat)2	-	-	-500	mV	IC=-10mA, IB=-1mA
VCE(sat)3	-	-	-750	mV	IC=-50mA, IB=-5mA
VBE(sat)	-	-	-750	mV	IC=-10mA, IB=-1mA
hFE1	40	-	-		VCE=-10V, IC=-1mA
hFE2	50	-	300		VCE=-10V, IC=-10mA
hFE3	45	-	-		VCE=-10V, IC=-50mA
hFE4	40	-	-		VCE=-10V, IC=-100mA

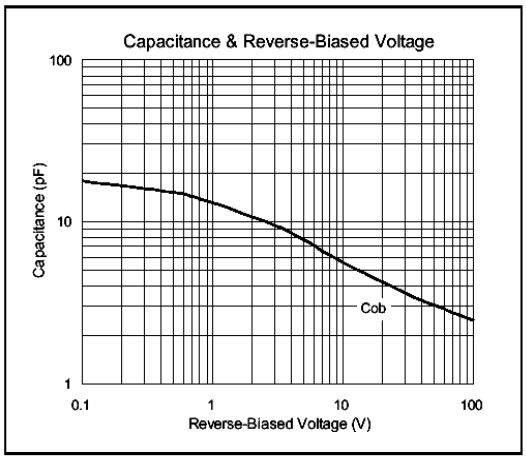
Classification of $h_{FE}2$

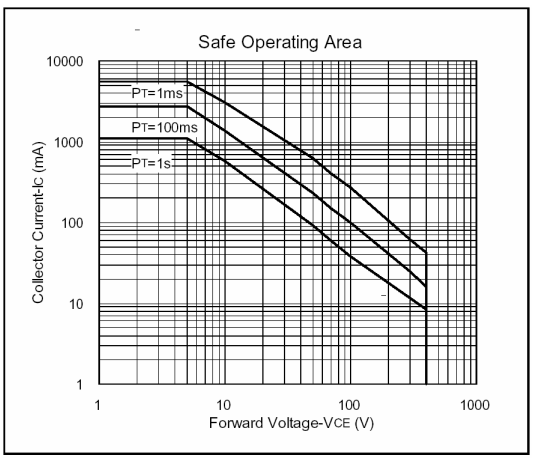
Rank	N	NS	SD	SUM
Range	50-300	70-300	70-210	120-300
VCE(sat)2:IC=-10mA, IB=-1mA	-	-	<200mV	-
hFE: VCE=3V,IC=100mA	-	>50	-	-

Characteristics Curve









Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165